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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **HASHIMOTO, Hiroshi et al.**

Group Art Unit: **2814**

Serial No.: **10/083,533**

Examiner: **Thao X. Le**

Filed: **February 27, 2002**

P.T.O. Confirmation No.: 6400

For: **SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND METHOD OF PRODUCING THE SAME**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
P.O. Box 1450
Alexandria, Va 22313-1450

May 6, 2003

Sir:

In response to the Office Action dated **February 6, 2003**, please amend the above-identified application as follows:

IN THE CLAIMS:

Amend claim 9 as indicated below:

9. (Amended) A semiconductor integrated circuit device comprising:

a substrate;

a nonvolatile memory device formed in a memory cell region of said substrate,

the nonvolatile memory device comprising:

a first active region covered with a tunnel insulating film;

a second active region formed next to the first active region and covered with

an insulating film;

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